

MASSACHUSETTS INSTITUTE OF TECHNOLOGY

Department of Electrical Engineering and Computer Science

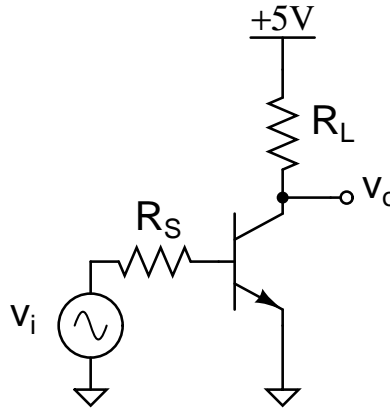
6.301 Solid State Circuits

Spring Term 2003  
Problem Set 2

Issued : February 7, 2003  
Due : Friday, February 14, 2003

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**Problem 1:** For the common-emitter amplifier shown below:



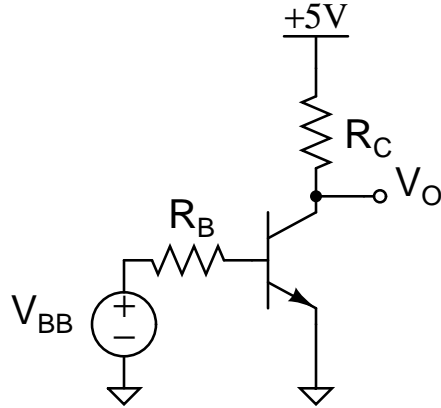
- (a) Find the small signal voltage gain  $v_o/v_i$  as a function of  $R_S$ ,  $R_L$ ,  $\beta$ ,  $V_A$ , and collector current  $I_C$ . Do not ignore  $r_o$  in this problem.
- (b) Find the small signal input resistance and output resistance. Do not include  $R_S$  in calculating the input resistance. Include  $R_L$ , however, in calculating the output resistance.

**Problem 2:** In this problem, we examine the effect of temperature on the bias stability. It is found that the  $I_S$  of the npn transistor shown below has a temperature coefficient ( $\frac{1}{I_S} \frac{dI_S}{dT}$ ) of 3300 ppm/ $^{\circ}\text{C}$  near 300 K. Also,  $\beta_F = 200$  at 300 K, and has a temperature coefficient ( $\frac{1}{\beta_F} \frac{d\beta_F}{dT}$ ) of 2000 ppm/ $^{\circ}\text{C}$ . You are given that  $I_S = 10^{-15}\text{A}$  at 300 K. Assume that the values of  $V_{BB}$ ,  $R_B$  and  $R_C$  are independent of temperature.

To simplify some of the math, you may assume that

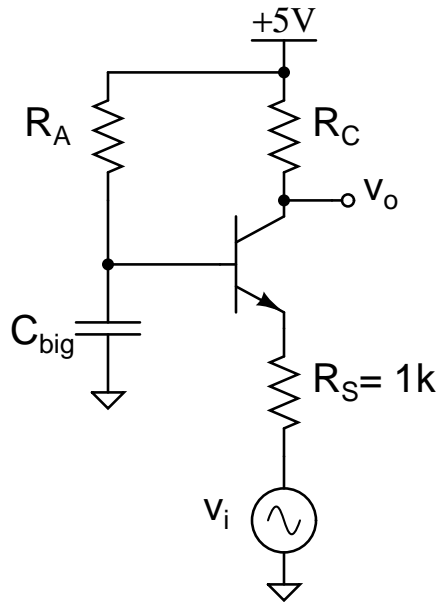
$$\frac{\partial(\log I_C)}{\partial T} \approx 0$$

- (a) Find the values of  $R_B$  and  $R_C$  to make  $I_C = 500\mu\text{A}$  and  $V_O = 2.5\text{V}$  at 300 K.
- (b) Derive the temperature coefficient of the collector current ( $\frac{1}{I_C} \frac{dI_C}{dT}$ ) at  $T = 300\text{K}$ .
- (c) Compute the temperature dependence of the quiescent output voltage ( $\frac{dV_O}{dT}$ ) in  $\text{V}/^{\circ}\text{C}$  at  $T = 300\text{K}$ .

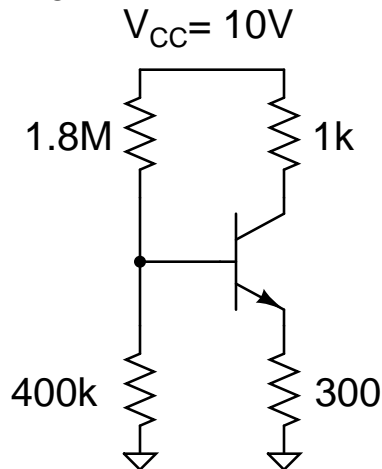


**Problem 3:** For the common-base amplifier circuit illustrated below:

- Determine the values of  $R_A$  and  $R_C$  so that  $I_C = 500\mu\text{A}$  and the small signal voltage gain  $v_o/v_i = 5$ . Assume that  $I_S = 10^{-15}\text{A}$  and  $\beta_F = \beta_o = 200$ . Be sure to make reasonable approximations in your calculations.
- Assuming that the temperature coefficient of  $V_{BE}$  is  $-2\text{mV}/^\circ\text{C}$ , compute the temperature coefficient of  $I_C$ . Assume that  $(1 + \beta_F)R_S \gg R_A$ . Express your answer as a function of the voltage drop  $V_S$  across  $R_S$ . What  $V_S$  do you need to reduce the temperature coefficient of  $I_C$  to  $500\text{ ppm}/^\circ\text{C}$ ?



**Problem 4:** Consider the following transistor circuit.



- (a) With  $V_{BE} = 0.7V$  and  $\beta = 400$ , calculate the transistor operating point (find  $I_C$  and  $V_{CE}$ ).
- (b) Due to a manufacturing mix-up, some of your transistors have  $\beta = 100$ . Find  $I_C$  for the new transistors.
- (c) Find new values for the base-biasing resistors so that  $I_C$  only changes by 10% when  $\beta$  falls from 400 to 100.
- (d) Refer again to the circuit in part (a). Due to temperature fluctuations in your operating environment,  $V_{BE}$  sometimes drops as low as 0.5V. Find  $I_C$  under this condition.
- (e) How should the transistor be biased so that  $I_C$  only changes by 10% if  $V_{BE}$  falls from 0.7V to 0.5V?

**Problem 5:** An EFCB (emitter-follower common-base) connection is illustrated below. Determine the overall small signal voltage gain  $v_o/v_i$ , input resistance, and output resistance. Assume  $\beta = 200$ . You may neglect  $r_o$  for this problem.

